Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A large-diameter SiC wafer, wherein a diameter is increased as a double structure of single crystal SiC and polycrystal SiC by planarly forming a film of polycrystal SiC in a flat plate shape around an outer circumference of a small diameter α-SiC single crystal wafer previously formed as a wafer; and

wherein a top and bottom surface of the small diameter α-SiC single crystal wafer is free of the polycrystal SiC.

2. (Currently Amended) The large-diameter SiC wafer according to claim 1, wherein at least two or more of said small-diameter α-SiC single crystal wafers are placed on a graphite plate.

3. (Original) The The large-diameter SiC wafer according to claim 1, wherein said polycrystal SiC is a β-SiC manufactured by a CVD method.

4. (Canceled)

5. (Currently Amended) A manufacturing method of a large-diameter SiC wafer comprising the steps of:

planarly placing a small diameter α-SiC single crystal wafer previously formed as a wafer on a graphite plate and simultaneously masking a surface of a substrate;

planarly forming a film of polycrystal SiC around an outer circumference of said wafer from its masking plane side ~~and integrating them; and thereafter~~by grinding the polycrystal SiC on the surface of the α-SiC single crystal wafer to manufacture an increased-

diameter SiC of a double structure in which the polycrystal SiC plate portion is formed around an outer circumference of the small-diameter α-SiC single crystal wafer; and

wherein a top and bottom surface of the small diameter α-SiC single crystal wafer is free of the polycrystal SiC.